3400/P

N-Channel Trench Power MOSFET

Features

- VDS=30V, ID=5.6A
- RDS(ON) <50 mΩ @ VGS = 2.5V
  RDS(ON <40mΩ @ VGS = 4.5V
  RDS(ON <35mΩ @ VGS = 10V
- High Power and Current Handing Capability
- Lead Free Product is Acquired
- Surface Mount Package

Application

- PWM Applications
- Load Switch
- Power Management

Package



SOT-23

Absolute Maximum Ratings (TC=25°Cunless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		30	V
V_{GSS}	Gate-Source Voltage		±12	V
I_D	Continuous Drain Current	T_C = 25°C	5.6	A
		T_C = 70°C	4.5	
P_D	Power Dissipation	T_C = 25°C	1.25	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		110	°C/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C

试用水印 www.superchip.cn